

IN THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. – 21. (canceled)

22. (original) A method comprising:

forming a first dielectric layer;

forming a bottom conductor on the first dielectric layer;

forming a second dielectric layer on the bottom conductor;

removing a section of the second dielectric layer to form a well;

removing a section of the bottom conductor to result in a via hole;

depositing a conductive material to form a top conductor on the second dielectric layer; and

depositing a conductive material in the well and the via hole to electrically connect the top conductor with the bottom conductor.

23. (currently amended) The method of claim 22 [[23]], wherein the via hole extends all the way through the bottom conductor.

24. (currently amended) The method of claim 23 [[24]], further comprising etching the second dielectric layer to result in a volume under the bottom conductor, wherein the volume has at least one overlap section that extends beyond a side wall of the via hole.

25. (currently amended) The method of claim 24 [[25]], wherein the volume under the bottom conductor is an anchor volume and wherein depositing a conductive material in the well and the via hole to electrically connect the top conductor with the bottom conductor further comprises depositing the conductive material to substantially fill the anchor

volume.

26. (new) The method of claim 22, wherein the conductive material that forms the top conductor on the second dielectric layer and the conductive material in the well and via hole that electrically connects the top conductor with the bottom conductor are regions of a continuous conductive volume that includes both the top conductor and the conductive material in the well and the via hole.

27. (new) The method of claim 22, wherein the conductive material that forms the top conductor on the second dielectric layer and the conductive material in the well and via hole that electrically connects the top conductor with the bottom conductor are deposited by the same deposition process.

28. (new) The method of claim 22, wherein removing the section of the second dielectric layer comprises removing material from the second dielectric layer with a laser.

29. (new) The method of claim 28, wherein the laser is a CO₂ laser with a wavelength of about 10.6 micrometers.

30. (new) The method of claim 22, wherein removing the section of the bottom conductor to create the via hole comprises removing material from the bottom conductor with a UV laser.

31. (new) The method of claim 22, wherein the well has a width in a range from about 62 micrometers to about 82 micrometers

32. (new) The method of claim 26, wherein the first and second dielectric layers,

the bottom conductor, and the continuous conductive volume are all parts of a package substrate, further comprising:

connecting a die to a first side of the package substrate; and

connecting a second side of the package substrate opposite to the first side to a printed circuit board, the package substrate electrically and mechanically

connecting the die to the printed circuit board.